$M_1 = 10^{16} m^{-3}$ Conduction Band $N_{\rm A} = 10^{23} \, {\rm m}^{-3}$ - Acceptor Level with acceptors, conduction will be by holes, i.e. Valence p-type Assuming all of the acceptor states are filled (a very safe assemption at T= 300 K), then $N_{\rm h} = N_{\rm A}$ And N.2 Ne= N. b) $m_{*}^{*} = m_{h}^{*} = m_{o}$ From equation 15.13 (it's not not too hard to derive) $N_e \cdot N_h = N_e \cdot N_V \exp(-\frac{E_s}{KT})$ Rearranging to solve for Eq, and using Known Ne and Nh values as well as the NC and No expressions $F_{g} = -K_{B} T \cdot l_{n} \left(\frac{N_{e} N_{h}}{N_{e} N_{V}} \right) = -(1.38 \cdot 10^{-23} T/k) (300 k) \cdot l_{n} \left(\frac{10^{9} \cdot 10^{32}}{N_{e} N_{V}} \right)$ $N_{c} = \frac{\partial (\partial \pi m_{e}^{*} K_{0}T)^{3/2}}{h^{3}} = \frac{\partial [\partial \pi (q. \|. \|\partial^{2/3} K_{0})(1.38 ||\partial^{-3/3} \overline{f_{k}})(3 | o 0 | k)]^{3/2}}{(6.63 ||\partial^{-3/3} \overline{f_{1}}|_{3})} = \partial [5| \cdot |\partial^{2/3} m^{-3/3} \overline{f_{1}}|_{3})$ $N_{v=} = \frac{\partial (\partial T m_{\mu}^{*} K_{0} T)^{2/2}}{L^{3}} = \partial .51 \cdot 10^{25} \text{ m}^{-3}$ $\Rightarrow E_{q} = (-4.14.10^{-31} \text{ J}) \cdot l_{2} \left[\frac{10^{32}}{(2.51.10^{37})^{3}} \right] = \left[1.79.10^{-19} \text{ J} = 1.1 \text{ eV} \right]$

c) The donor impurities will, is a sense compensate 1-for-1 with acceptors, so the semiconductor with $N_a = 10^{23} \text{ m}^{-3}$ and $N_D = 5 \cdot 10^{22} \text{ m}^{-3}$ will act like a semiconductor doped with $N_{A=}(10^{23} \text{ m}^{-3}) - (5 \cdot 10^{22} \text{ m}^{-3}) = 5 \cdot 10^{22} \text{ m}^{-3}$ Then Nn= Na= 5.10 ad m-3 $N_{e=} \frac{N^{2}}{N_{e}} = \frac{(10^{16} n^{-3})^{2}}{(5 \cdot 10^{22} n^{-3})} = [2 \cdot 10^{9} m^{-3}]$ Intuitively, we know Eq. shouldn't change by doping (and the equation will tell you that). Eg=[1. | eV]

 $\partial = \partial N_1 = 10'' \text{ cm}^3 = 10^{17} \text{ m}^{-3}$ Group II elevent -> acceptor $N_{A} = 10^{17} \text{ cm}^{-3} = 10^{23} \text{ m}^{-3}$ Using the assumptions discussed in problem 1: $\frac{N_{e}}{N_{e}} = \frac{N_{e}}{M_{e}} = \frac{(10^{17} m^{-3})^{2}}{10^{23} m^{-3}} = \frac{10^{11} m^{-3}}{10^{11} m^{-3}}$ b) In addition to the equilibrium concentrations expected from part (a), there will be 10° more holes and 10° more electrons per GM³, $10^{9} \text{ cm}^{-3} = 10^{15} \text{ m}^{-3}$ $M_{h} = 10^{23} \text{ m}^{-3} + 10^{15} \text{ m}^{-3} = 1.00000001 \text{ (10}^{23} \text{ m}^{-3} \text{ (not much change!)}$ change in hole conc. = $\frac{10^{23} + 10^{15}}{10^{23}} = [1.00000001, \text{ or } 1 \text{ in } 100 \text{ million}]$ $N_{e} = 10'' m^3 + 10^{15} m^3 = 1.000 | 10'^5 m^{-3}$ Change in elec. conc. = $\frac{10'' + 10'^5}{10''} = [1000]$, or ten thousand fold increase () As we saw in part (b), the hole conentration is pretty unaffected by the light, so the conc. of holes after turning off the light basically remains constant at $N_h = 10^{23} \text{ m}^{-3}$ The minority carrier (electron) excess concentration falls offas $exp(-\frac{\pi}{2})$, After one milliserond the excess concentration is $N_{\text{excess}} = (10^{15} - 10^{"}) \cdot exp(-\frac{10^{-3} \text{ s}}{3 \cdot 10^{-4} \text{ s}}) = 3.57 \cdot 10^{13} \text{ m}^{-3}$ Ne= 10"m-3+ 3.57.10"m-3 = 3.58.10"m-3/

 $M_e^* = 0.35 \text{ Mo} \qquad N_A = 10^{18} \text{ cm}^3 = 10^{24} \text{ m}^{-3}$ $m_{h}^{*} = 0.5 m_{o}$ $A_{0} = 10^{16} \text{ cm}^{3} = 10^{22} \text{ m}^{-3}$ $E_g = 2.25 eV$ $E_{r=9}$ From equation 15.14; $N_{i} = \left(N_{c} \cdot N_{v}\right) \exp\left(-\frac{E_{d}}{2K_{e}T}\right) = \frac{2\left(\partial T \cdot K_{e}T\right)^{4}}{h^{2}} \cdot \left(M_{e}^{*} \cdot M_{h}^{*}\right)^{34} \cdot \exp\left(-\frac{E_{d}}{2K_{e}T}\right)$ $\frac{1}{N_{1}} = \frac{1}{(6.63 \cdot 10^{-34} \text{ J} \cdot \text{S})^{3}} [(0.35)(0.5)(9.11 \cdot 10^{-31} \text{ kg})^{2}]^{3/2} \exp\left(-\frac{2.25 \text{ eV}}{2 \text{ (kgT)}}\right)$ N: = 8,57.105 m-3 <u>Note</u> small value for N:, as we should expect for a large bandgap semiconductor $V_{o} = \frac{K_{BT}}{e} l_{o} \left(\frac{N_{A} \cdot N_{O}}{N^{2}} \right)$ $= \frac{(1.38 \cdot 10^{-19} \text{ K})(300 \text{ K})}{(114 \cdot 10^{-19} \text{ cm}^{-1})} \left(\frac{(10^{24} \text{ m}^{-3}) \cdot (10^{22} \text{ m}^{-3})}{(8.57 \cdot 10^{5} \text{ m}^{-3})^{2}} \right)$ = 2.03 V/

4. Color amitted, from an LED is related to the energy of the bandapp, since this is the energy of aphaton emitted when an electron and a hole recombine for G.P. Ez=23eV for GaN, Eg= 3.4eV As we replace P with N, Eq will increase from 2.3eV-3.4. $\partial.3eV$ photons correspond to a Wavelength of $\lambda = \frac{hc}{E} = \frac{(6.63\cdot10^{-34} \text{ J}.5)(3\cdot10^{-8} \text{ M}s)}{(2.3ev)(1.6\cdot10^{-14} \text{ Mev})} = 539 \text{ nm} (green)$ 3.4eV, $\lambda = \frac{bc}{E} = 365 \text{ nm}$ (blue) So the LED would go from green to blue as we replace phosphorous with nitrogen.